PLASMA PROCESSING APPARATUS AND GAS SUPPLY METHOD

Abstract

There is provided a plasma processing apparatus comprising: a plasma processing chamber having a substrate support configured to support a substrate; a shower head having a plurality of gas inlets configured to introduce a gas into respective regions in the plasma processing chamber; a gas supply configured to supply a gas to the plurality of gas inlets; a plasma generator configured to generate a plasma of the gas; and a controller configured to control at least the gas supply. The gas supply includes: a gas unit configured to supply a common gas to the plurality of gas inlets; and an injection unit configured to supply an injection gas to the selected gas inlet among the plurality of gas inlets, and the controller controls the injection unit so that two or more types of injection gases are supplied to two different ones of the plurality of gas inlets.

FIG. 1